

Product Overview

NTD360N80S3Z: MOSFET – Power, N-Channel, SUPERFET® III, 800 V, 13 A, 360 mΩ, DPAK

For complete documentation, see the data sheet.

800 V SUPERFET III MOSFET is ON Semiconductor's high performance MOSFET family offering 800 V breakdown voltage. New 800 V SUPERFET III MOSFET which is optimized for primary switch of flyback converter, enables lower switching losses and case temperature without sacrificing EMI performance thanks to its optimized design. In addition, internal Zener Diode significantly improves ESD capability. This new family of 800 V SUPERFET III MOSFET enables to make more efficient, compact, cooler and more robust applications because of its remarkable performance in switching power applications such as Laptop adapter, Audio, Lighting, ATX power and industrial power supplies.

Features

- Typ. RDS(on) = 300 mΩ
- Ultra Low Gate Charge (Typ. Qg = 25.3 nC)
- Low Stored Energy in Output Capacitance (Eoss = 2.72 μJ @ 400 V)
- 100% Avalanche Tested
- ESD Improved Capability with Zener Diode
- RoHS Compliant

Applications

- Adapters / Chargers
- LED Lighting
- AUX Power
- Audio
- Industrial Power

Benefits

- Low switching loss, High efficiency
- Good EMI performance
- Improved ESD capability with internal Zener Diode

End Products

- Adapters / Chargers
- LED Lighting
- AUX Power
- Audio
- Industrial Power

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{DS(BR)} Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Package Type
NTD360N80S3Z	0.806	Pb-free Halide free	NEW	N-Channel	Single	800	±30	3.8	13	96			360		25.3	1143	DPAK-3 / TO-252-3

For more information please contact your local sales support at www.onsemi.com.

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